

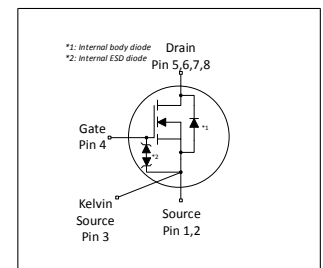
MOSFET

700V CoolMOS™ P7 Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

The latest CoolMOS™ P7 is an optimized platform tailored to target cost sensitive applications in consumer markets such as charger, adapter, lighting, TV, etc.

The new series provides all the benefits of a fast switching Superjunction MOSFET, combined with an excellent price/performance ratio and state of the art ease-of-use level. The technology meets highest efficiency standards and supports high power density, enabling customers going towards very slim designs.



Features

- Extremely low losses due to very low FOM $R_{DS(on)} * Q_g$ and $R_{DS(on)} * E_{oss}$
- Excellent thermal behavior
- Integrated ESD protection diode
- Low switching losses (E_{oss})
- Fully qualified acc. JEDEC for Industrial Applications

Benefits

- Cost competitive technology
- Lower temperature
- High ESD ruggedness
- Enables efficiency gains at higher switching frequencies
- Enables high power density designs and small form factors

Potential applications

Recommended for Flyback topologies in Chargers and Adapters

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.



Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_J=25^{\circ}C$	700	V
$R_{DS(on),max}$	1.4	Ω
$Q_{g,typ}$	4.7	nC
$I_{D,pulse}$	8.2	A
$E_{oss} @ 400V$	0.6	μJ
$V_{(GS)th,typ}$	3	V
ESD class (HBM)	1C	

Type / Ordering Code	Package	Marking	Related Links
IPLK70R1K4P7	ThinPAK 5x6 SMD	70R1K4P7	see Appendix A

Table of Contents

Description	1
Maximum ratings	3
Thermal characteristics	3
Electrical characteristics	4
Electrical characteristics diagrams	6
Test Circuits	10
Package Outlines	11
Appendix A	12
Revision History	13
Trademarks	13
Disclaimer	13

1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	3.9 2.4	A	$T_C = 20^\circ\text{C}$ $T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	8.2	A	$T_C=25^\circ\text{C}$
Application (Flyback) relevant avalanche current, single pulse ³⁾	I_{AS}	-	2.4	-	A	measured with standard leakage inductance of transformer of $5\mu\text{H}$
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS} = 0 \dots 400\text{V}$
Gate source voltage	V_{GS}	-16 -30	-	16 30	V	static; AC ($f > 1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	22.7	W	$T_C=25^\circ\text{C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	5.7	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	8.2	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt ⁴⁾	dv/dt	-	-	1	V/ns	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j=25^\circ\text{C}$
Maximum diode commutation speed ⁴⁾	di/dt	-	-	50	A/ μs	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j=25^\circ\text{C}$
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{ min}$

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction	R_{thJC}	-	-	5.5	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	$^\circ\text{C/W}$	Device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	62	$^\circ\text{C/W}$	Device on $40\text{mm} \times 40\text{mm} \times 1.5$ epoxy PCB FR4 with 6cm^2 (one layer $70\mu\text{m}$ thickness) copper area for drain connection and cooling. PCB is vertical without airflow.
Soldering temperature, wave- & reflow soldering allowed	T_{solid}	-	-	260	$^\circ\text{C}$	reflow MSL1

¹⁾ Limited by $T_{j,max}$. $T_j = 20^\circ\text{C}$. Maximum duty cycle $D=0.5$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Proven during verification test. Avalanche value is assuming only the energy from a Flyback transformer leakage inductance is transferred to the MOSFET. For less common avalanche situations it is recommended to contact Infineon for more information. For explanation please read AN - CoolMOS™ 700V P7.

⁴⁾ $V_{DClink}=400\text{V}$; $V_{DS,peak} < V_{(BR)DSS}$; identical low side and high side switch with identical R_G

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	700	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	2.50	3	3.50	V	$V_{DS}=V_{GS}, I_D=0.04mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=700V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=700V, V_{GS}=0V, T_j=150^\circ C$
Gate-source leakage current incl. Zener diode	I_{GSS}	-	-	1	μA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.15	1.40	Ω	$V_{GS}=10V, I_D=0.7A, T_j=25^\circ C$ $V_{GS}=10V, I_D=0.7A, T_j=150^\circ C$
Gate resistance	R_G	-	1.6	-	Ω	$f=1\text{ MHz}, \text{open drain}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	158	-	pF	$V_{GS}=0V, V_{DS}=400V, f=250kHz$
Output capacitance	C_{oss}	-	3	-	pF	$V_{GS}=0V, V_{DS}=400V, f=250kHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	9	-	pF	$V_{GS}=0V, V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	113	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=10.2\Omega$
Rise time	t_r	-	4.9	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=10.2\Omega$
Turn-off delay time	$t_{d(off)}$	-	63	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=10.2\Omega$
Fall time	t_f	-	61	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=10.2\Omega$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	0.7	-	nC	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$
Gate to drain charge	Q_{gd}	-	1.7	-	nC	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$
Gate charge total	Q_g	-	4.7	-	nC	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$
Gate plateau voltage	$V_{plateau}$	-	4.3	-	V	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V, I_F=0.9A, T_j=25^{\circ}C$
Reverse recovery time	t_{rr}	-	275	-	ns	$V_R=400V, I_F=0.5A, di_F/dt=50A/\mu s$
Reverse recovery charge	Q_{rr}	-	0.4	-	μC	$V_R=400V, I_F=0.5A, di_F/dt=50A/\mu s$
Peak reverse recovery current	I_{rrm}	-	6	-	A	$V_R=400V, I_F=0.5A, di_F/dt=50A/\mu s$

4 Electrical characteristics diagrams

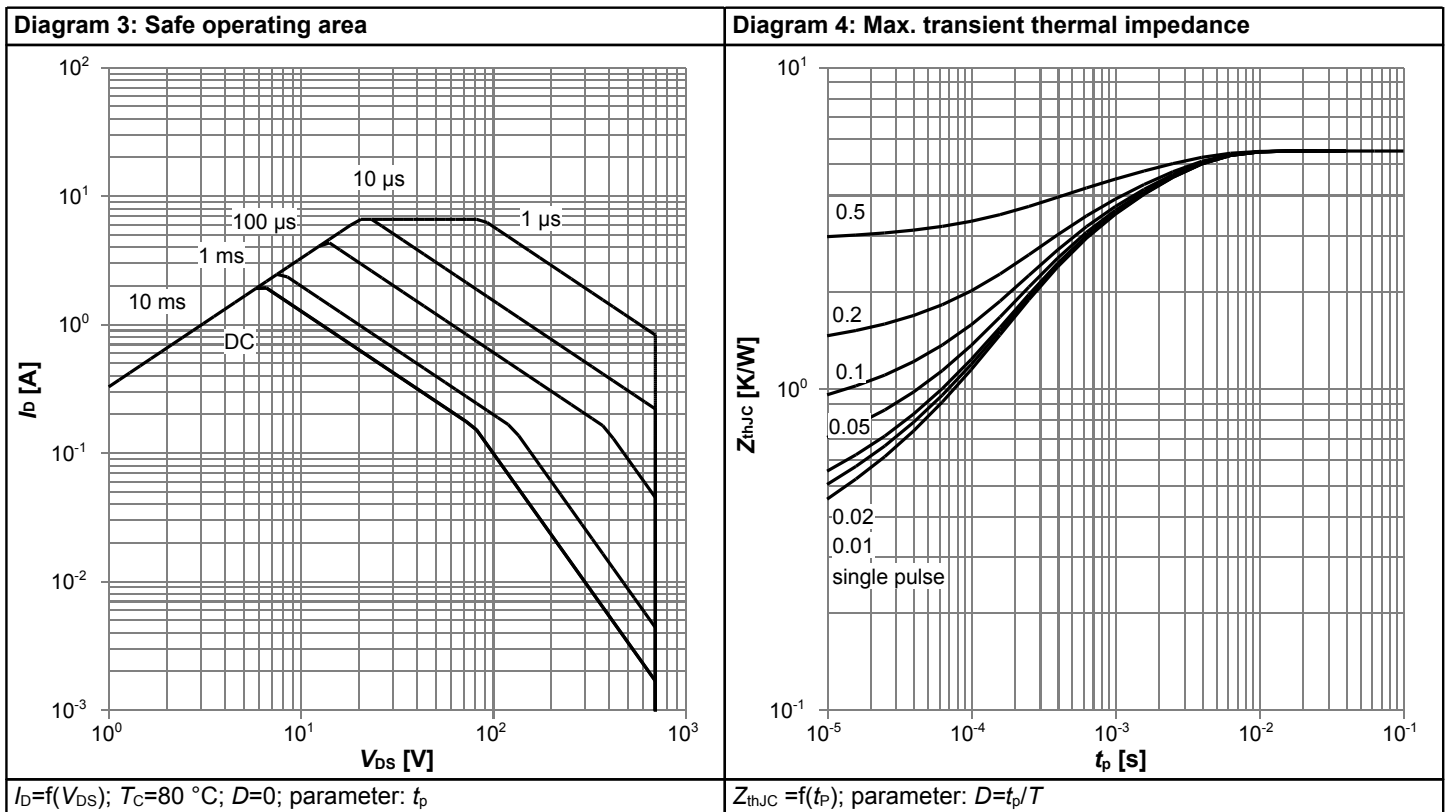
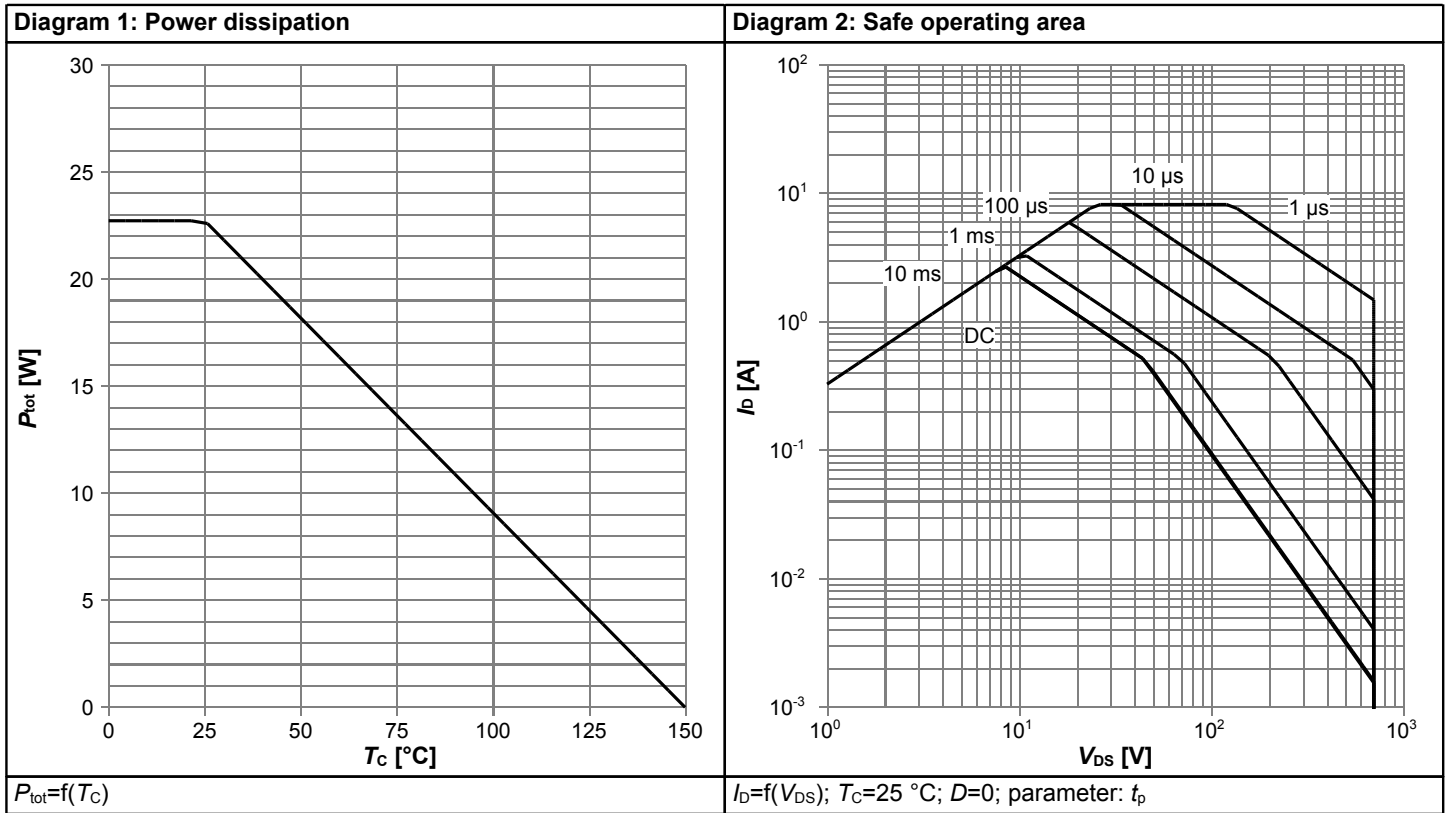
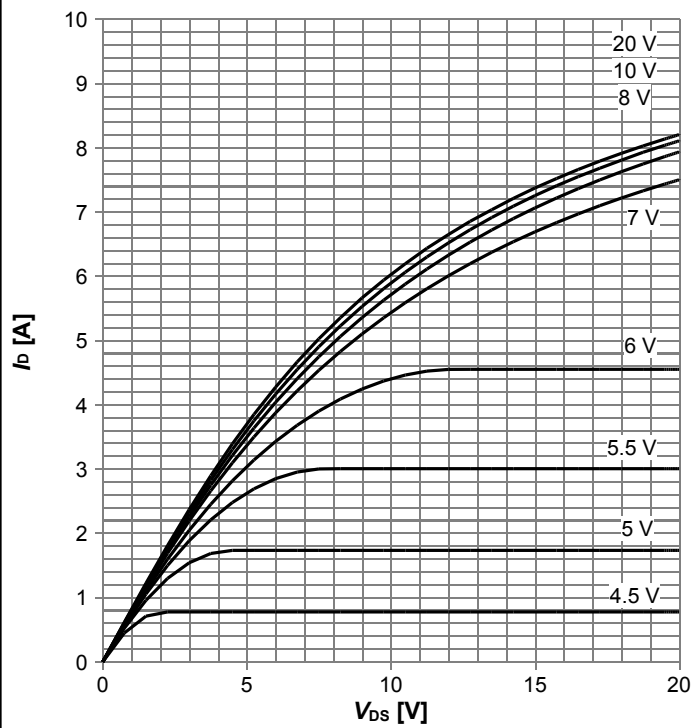
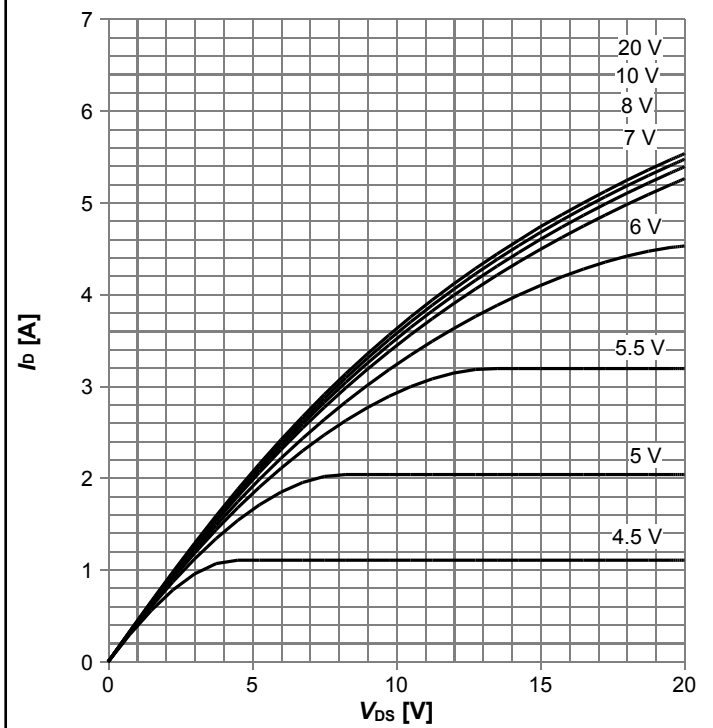


Diagram 5: Typ. output characteristics



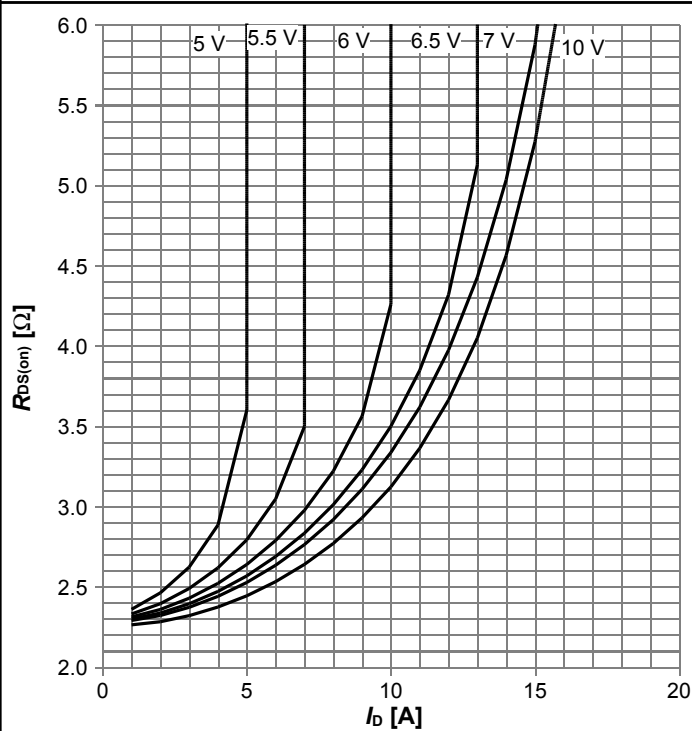
$I_D=f(V_{DS}); T_j=25\text{ °C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. output characteristics



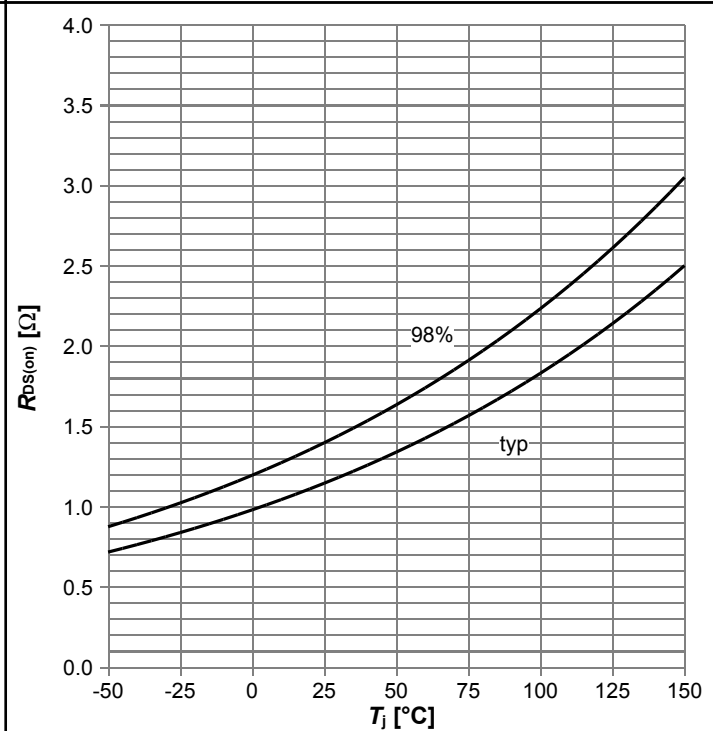
$I_D=f(V_{DS}); T_j=125\text{ °C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



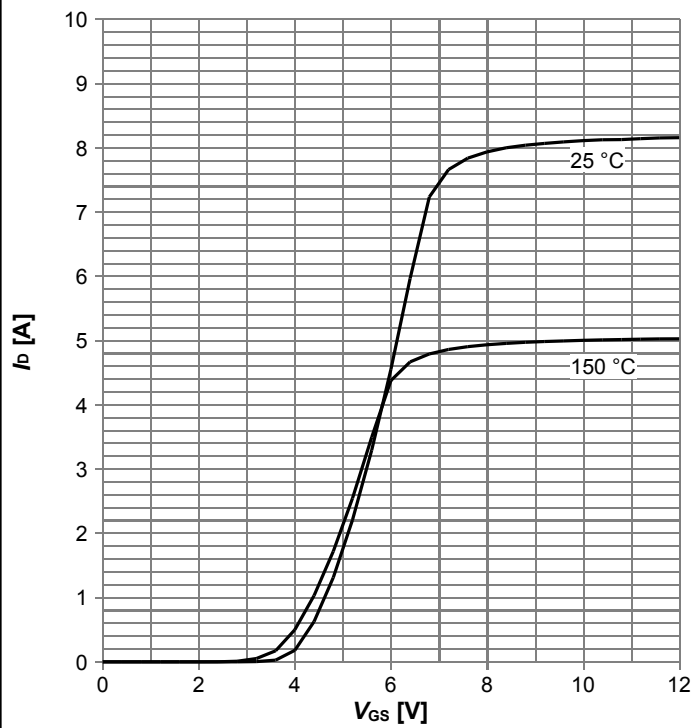
$R_{DS(on)}=f(I_D); T_j=125\text{ °C}; \text{parameter: } V_{GS}$

Diagram 8: Drain-source on-state resistance



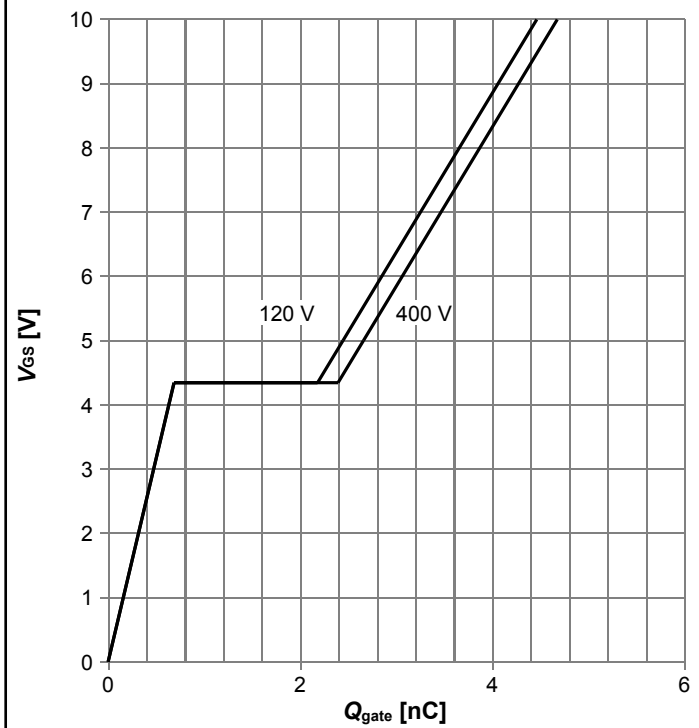
$R_{DS(on)}=f(T_j); I_D=0.7\text{ A}; V_{GS}=10\text{ V}$

Diagram 9: Typ. transfer characteristics



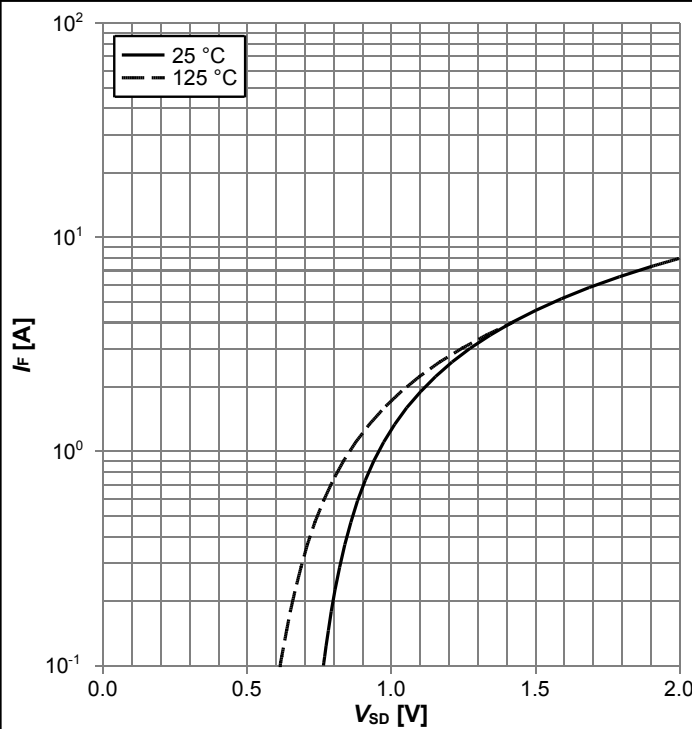
$I_D=f(V_{GS}); V_{DS}=20V$; parameter: T_j

Diagram 10: Typ. gate charge



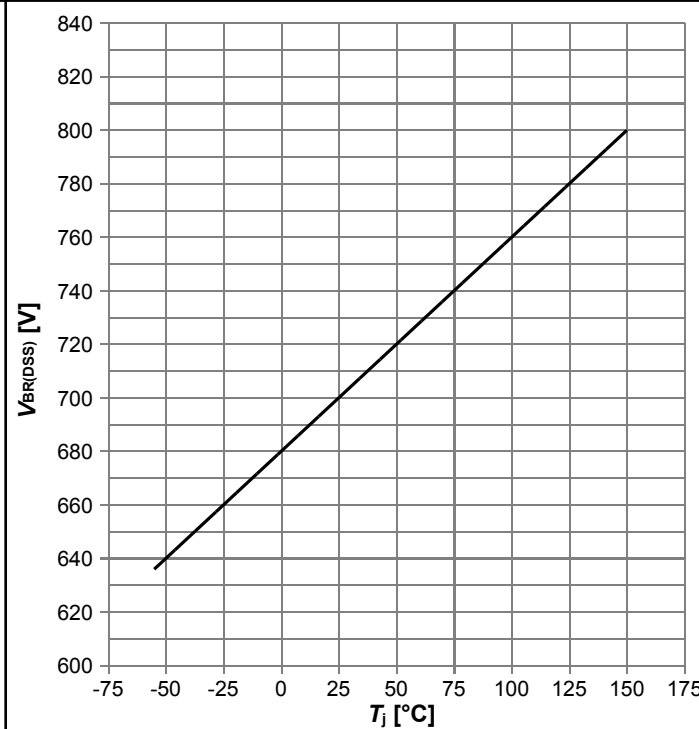
$V_{GS}=f(Q_{gate}); I_D=0.5$ A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



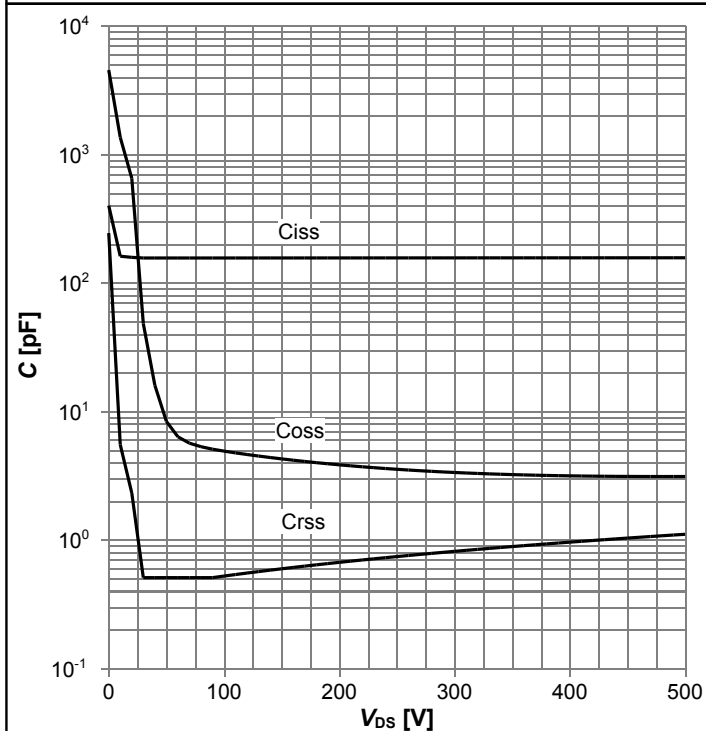
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Drain-source breakdown voltage



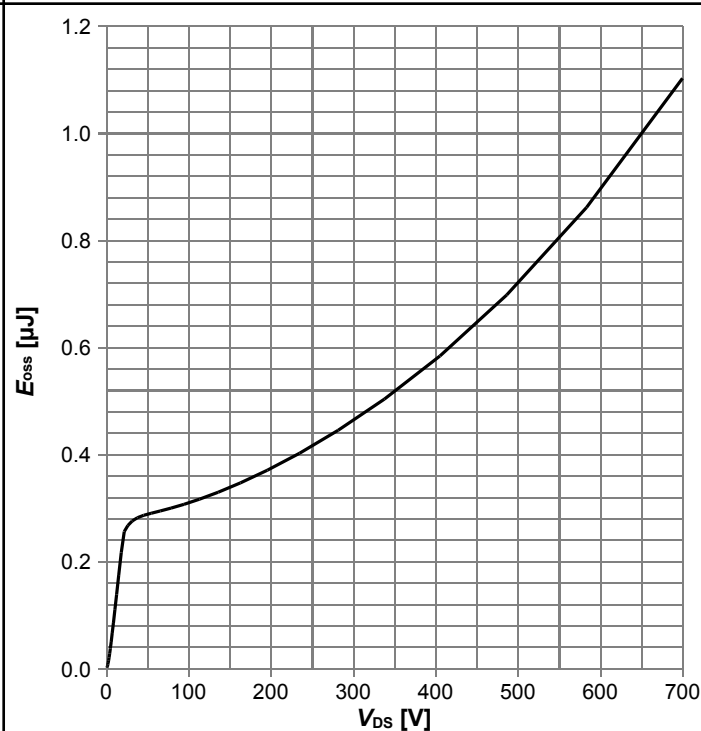
$V_{BR(DSS)}=f(T_j); I_D=1$ mA

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=250\text{ kHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

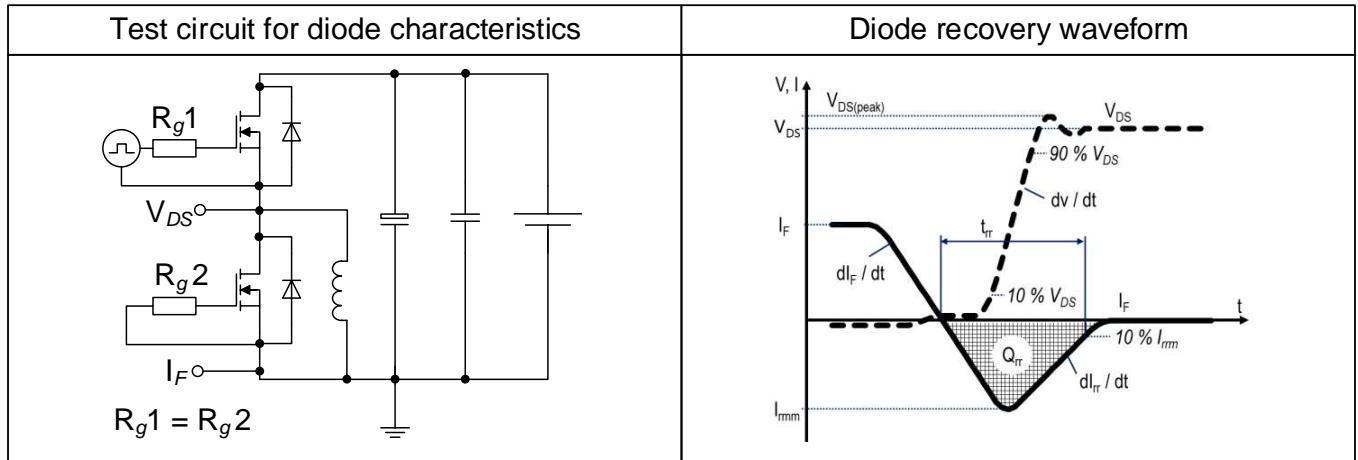


Table 9 Switching times

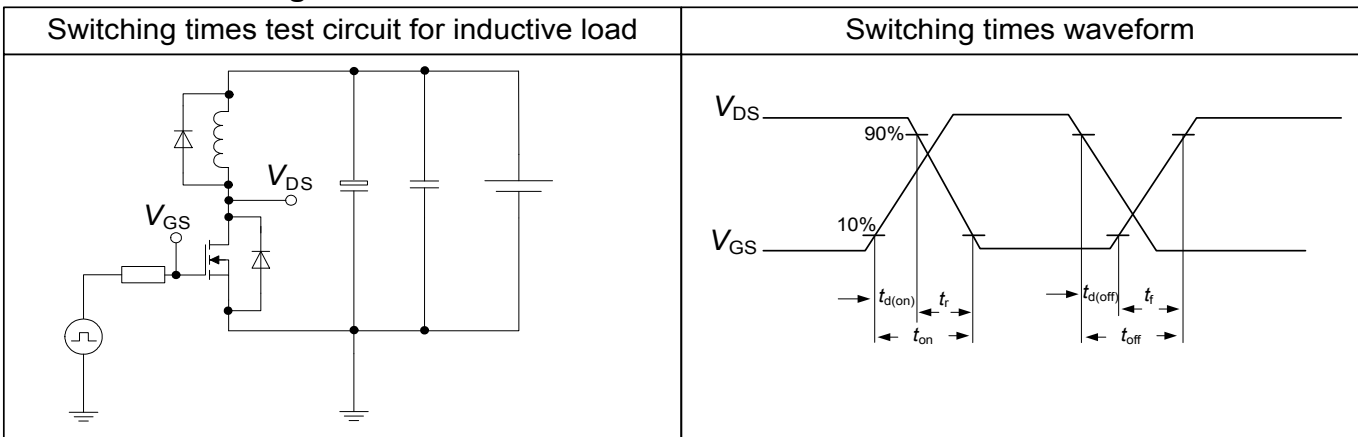
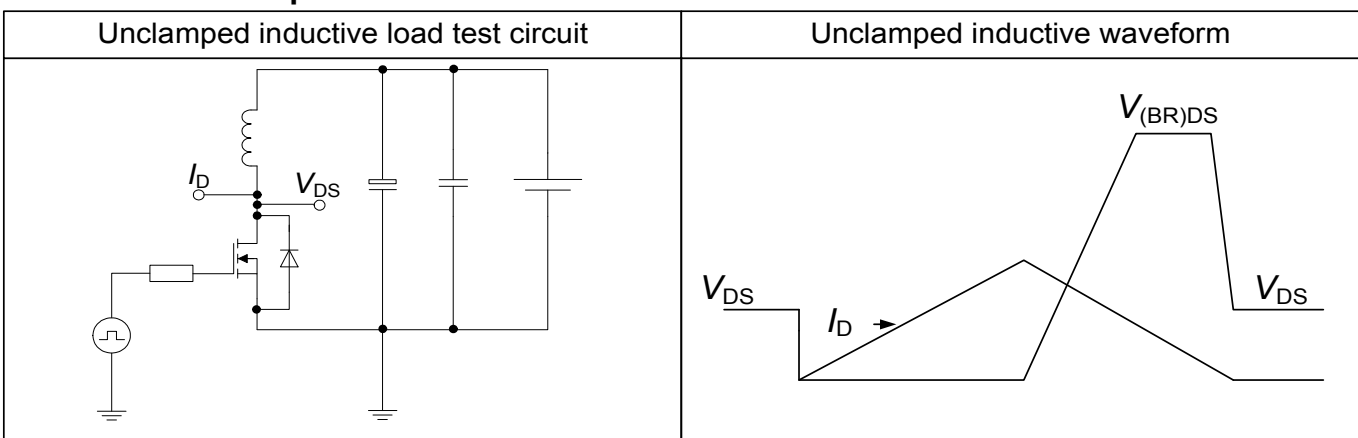
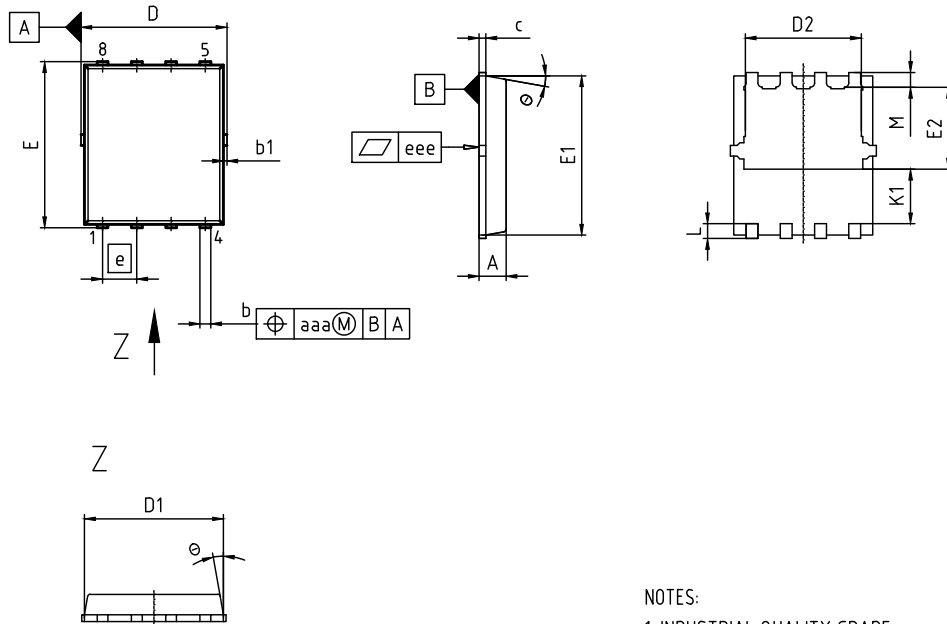


Table 10 Unclamped inductive load



6 Package Outlines



- NOTES:
1. INDUSTRIAL QUALITY GRADE
 2. ALL DIMENSIONS REFER TO JEDEC STANDARD MO240A NOT INCLUDE MOLD FLASH
 3. REMOVAL ON MOLD GATE, INTRUSION 0.1mm; PROPRUSION 0.1mm
 4. ALL METAL SURFACE ARE PLATED EXCEPT AREA OF CUT

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.34	0.54	0.013	0.021
b1	0.03	0.23	0.001	0.009
c	0.15	0.35	0.006	0.014
D	5.15	5.51	0.203	0.217
D1	4.95	5.35	0.195	0.211
D2	4.20	4.40	0.165	0.173
E	5.95	6.35	0.234	0.250
E1	5.70	6.10	0.224	0.240
E2	2.93	3.13	0.115	0.123
e	1.27		0.050	
N	8		8	
K1	1.92	2.12	0.076	0.083
L	0.45	0.65	0.018	0.026
M	0.45	0.65	0.018	0.026
φ	8.5°	12°	8.5°	12°
aaa	0.25		0.010	
eee	0.08		0.003	

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REVISION
01

Figure 1 Outline ThinPAK 5x6 SMD, dimensions in mm/inches - Industrial Grade

7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ P7 Webpage: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPLK70R1K4P7

Revision: 2018-09-26, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2018-09-26	Release of final version

Trademarks

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Information

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